

TRANSISTOR (NPN)	SOT-23 Plastic-Encapsulate Transistors

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 100 μ A, IE=0	80			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 1mA, IB=0	80			V
Emitter-base breakdown voltage	V(BR)EBO	IE=100 μ A, IC=0	4			V
Collector cut-off current	ICBO	VCB=80 V , IE=0			0.1	μ A
Collector cut-off current	ICEO	VCE=60V , IB=0			1	μ A
Emitter cut-off current	IEBO	VEB= 3V , IC=0			0.1	μ A
DC current gain	hFE	VCE=1V, IC= 10mA	100		400	
	hFE	VCE=1V, IC= 100mA	100			
Collector-emitter saturation voltage	VCE(sat)	IC=100 mA, IB= 10mA			0.25	V
Base-emitter saturation voltage	VBE(sat)	IC=100 mA, IB= 10mA			1.2	V
Transition frequency	fT	VCE=2V, IC= 10mA f=100MHz	100			MHz

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

